

MBR20L45CTG, MBRF20L45CTG

SWITCHMODE™ Power Rectifier 45 V, 20 A

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 150°C Operating Junction Temperature
- 20 A Total (10 A Per Diode Leg)
- Guard-Ring for Stress Protection

Applications

- Power Supply - Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes:
260°C Max. for 10 Seconds
- Shipped 50 Units Per Plastic Tube
- This is a Pb-Free Device*

MAXIMUM RATINGS

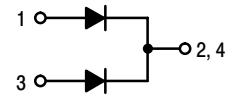
Please See the Table on the Following Page



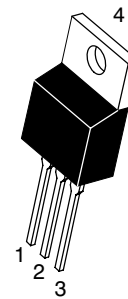
ON Semiconductor®

<http://onsemi.com>

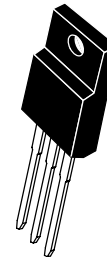
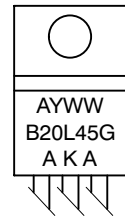
DUAL SCHOTTKY BARRIER RECTIFIERS 20 AMPERES, 45 VOLTS



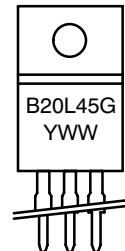
MARKING DIAGRAMS



TO-220
CASE 221A
PLASTIC



TO-220
CASE 221D
STYLE 3



B20L45 = Device Code
A = Assembly Location
Y = Year
WW = Work Week
AKA = Polarity Designator
G = Pb-Free Device

ORDERING INFORMATION

Device	Package	Shipping
MBR20L45CTG	TO-220 (Pb-Free)	50 Units/Rail
MBRF20L45CTG	TO-220FP (Pb-Free)	50 Units/Rail

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR20L45CTG, MBRF20L45CTG

MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
Average Rectified Forward Current (Rated V_R) $T_C = 141^\circ\text{C}$	$I_{F(AV)}$	10	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz)	I_{FRM}	20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	180	A
Operating Junction Temperature (Note 1)	T_J	-55 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/ μs
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

THERMAL CHARACTERISTICS

Maximum Thermal Resistance (MBR20L45CTG)	Junction-to-Case	$R_{\theta JC}$	1.9	$^\circ\text{C/W}$
	Junction-to-Ambient	$R_{\theta JA}$	45	
(MBRF20L45CTG)	Junction-to-Case	$R_{\theta JC}$	2.2	

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 10\text{ A}$, $T_C = 25^\circ\text{C}$) ($I_F = 10\text{ A}$, $T_C = 125^\circ\text{C}$) ($I_F = 20\text{ A}$, $T_C = 25^\circ\text{C}$) ($I_F = 20\text{ A}$, $T_C = 125^\circ\text{C}$)	V_F	0.50 0.47 0.63 0.62	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 25^\circ\text{C}$) (Rated DC Voltage, $T_C = 125^\circ\text{C}$)	i_R	0.5 170	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.
- Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

MBR20L45CTG, MBRF20L45CTG

TYPICAL CHARACTERISTICS

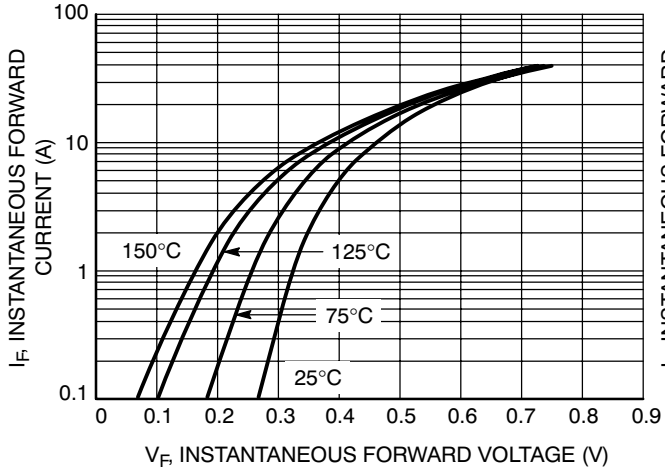


Figure 1. Typical Forward Voltage

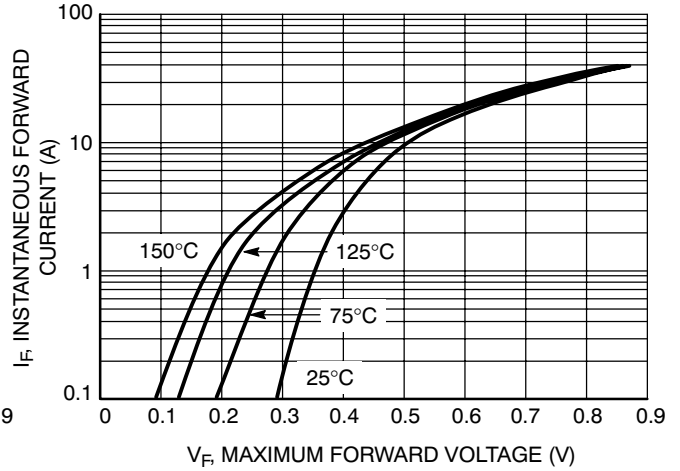


Figure 2. Maximum Forward Voltage

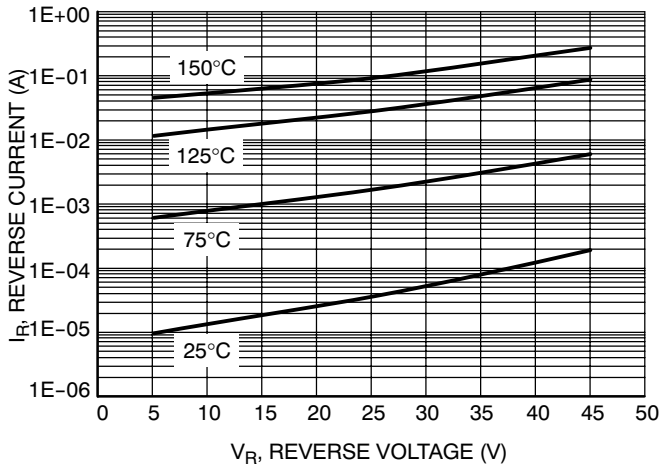


Figure 3. Typical Reverse Current

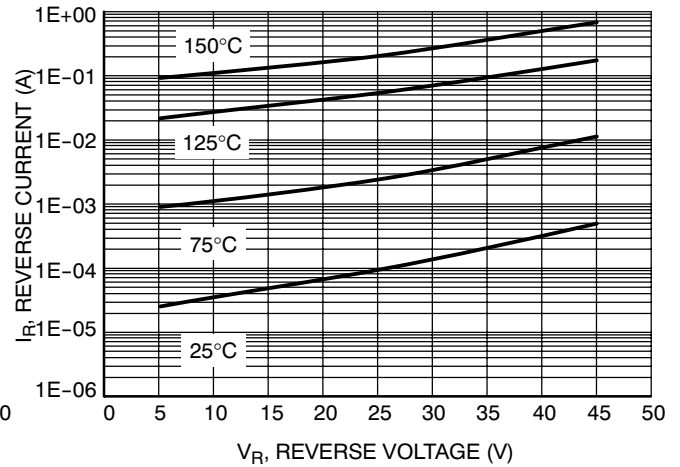


Figure 4. Maximum Reverse Current

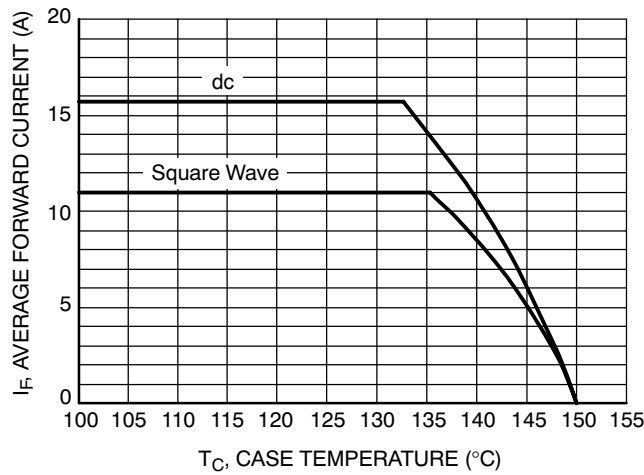


Figure 5. Current Derating

MBR20L45CTG, MBRF20L45CTG

TYPICAL CHARACTERISTICS

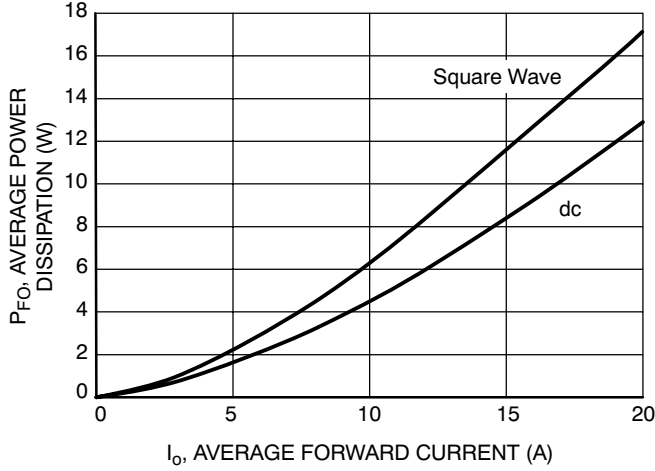


Figure 6. Forward Power Dissipation

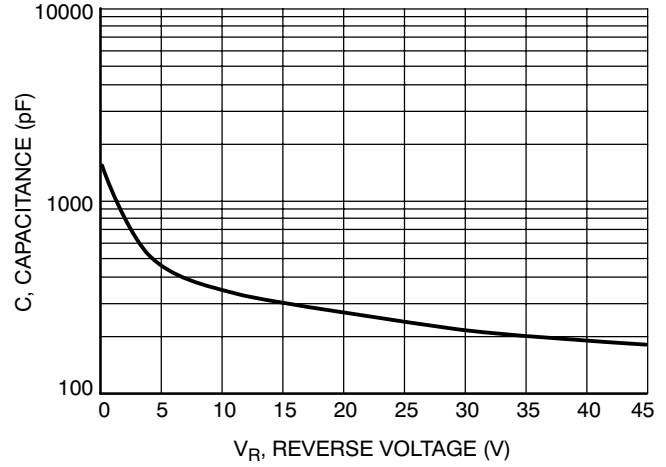


Figure 7. Typical Capacitance

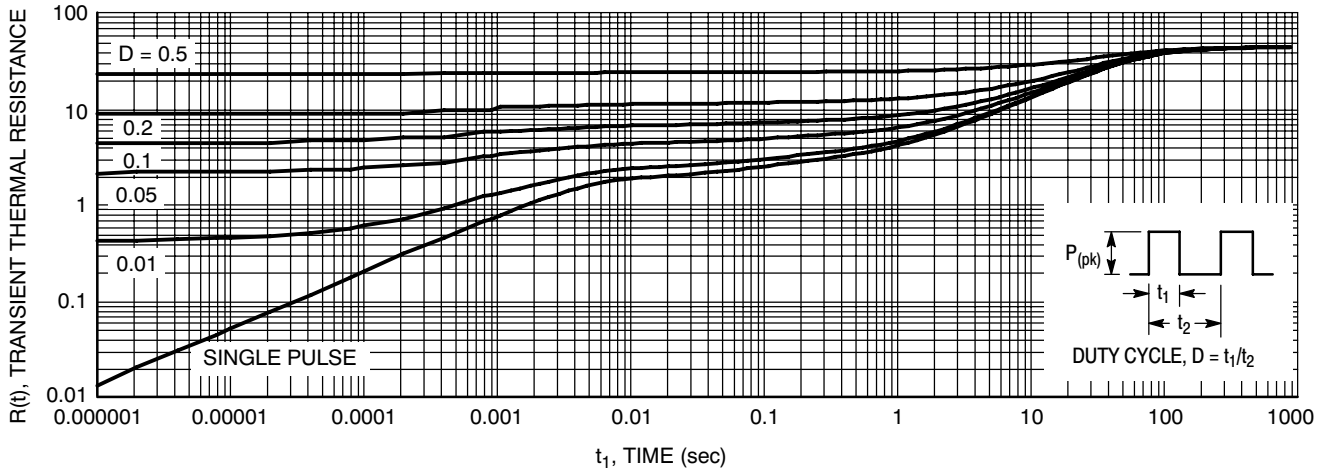


Figure 8. Thermal Response Junction-to-Ambient for MBR20L45CTG

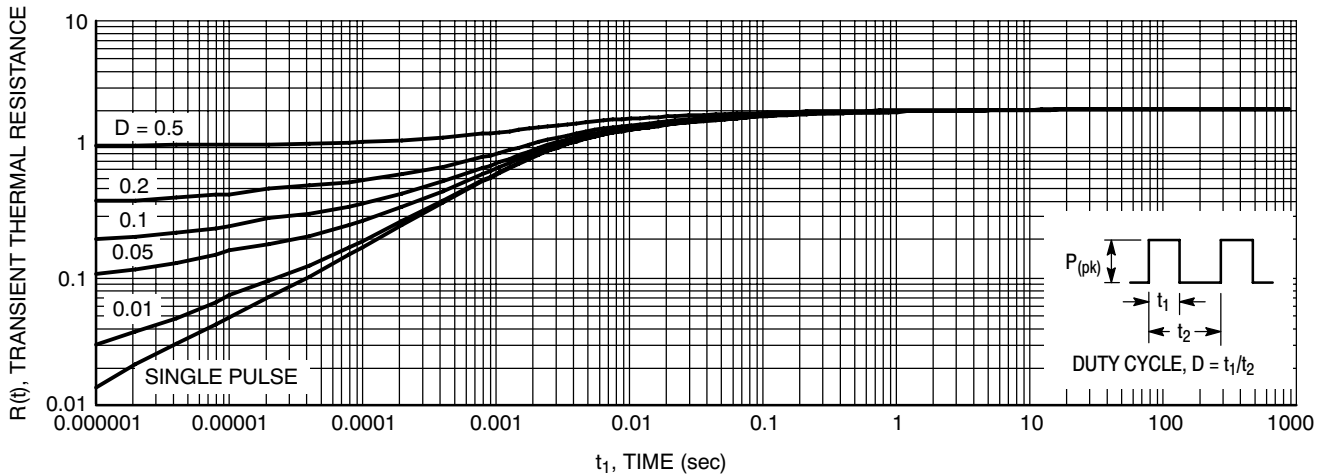


Figure 9. Thermal Response Junction-to-Case for MBR20L45CTG

MBR20L45CTG, MBRF20L45CTG

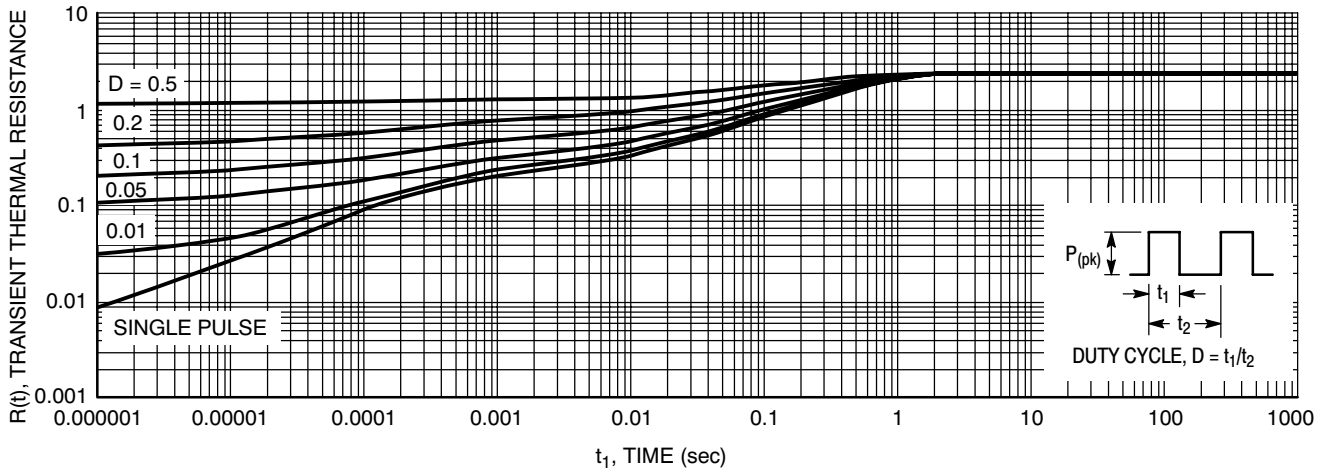
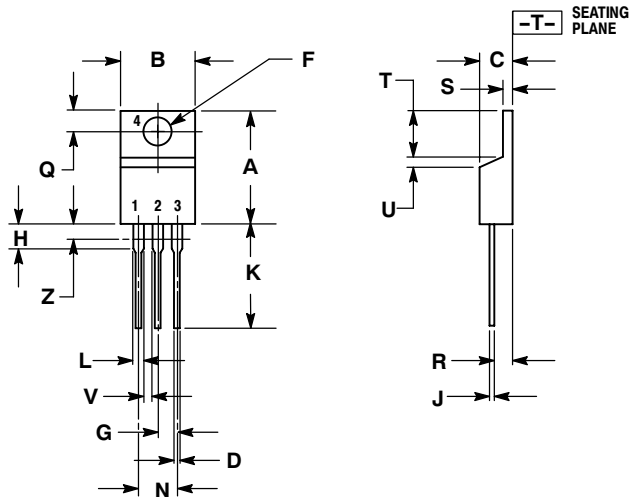


Figure 10. Thermal Response Junction-to-Case for MBRF20L45CTG

MBR20L45CTG, MBRF20L45CTG

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AD

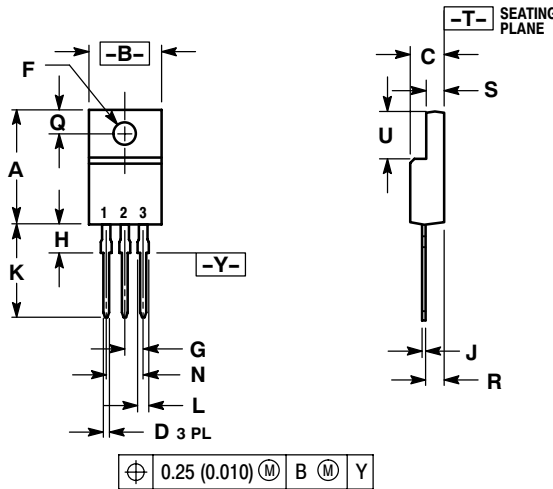


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

TO-220 FULLPAK CASE 221D-03 ISSUE H



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH
3. 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.625	0.635	15.88	16.12
B	0.408	0.418	10.37	10.63
C	0.180	0.190	4.57	4.83
D	0.026	0.031	0.65	0.78
F	0.116	0.119	2.95	3.02
G	0.100 BSC		2.54 BSC	
H	0.125	0.135	3.18	3.43
J	0.018	0.025	0.45	0.63
K	0.530	0.540	13.47	13.73
L	0.048	0.053	1.23	1.36
N	0.200 BSC		5.08 BSC	
Q	0.124	0.128	3.15	3.25
R	0.099	0.103	2.51	2.62
S	0.101	0.113	2.57	2.87
U	0.238	0.258	6.06	6.56

STYLE 3:

1. ANODE
2. CATHODE
3. ANODE

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